

**SANYO****DFH10T**

Diffused Junction Type Silicon Diode

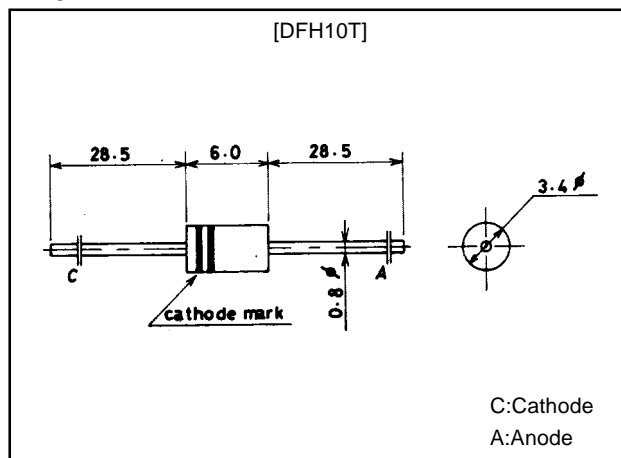
**1.0A Power Rectifier****Features**

- High-speed switching use.
- Plastic molded structure.
- Reverse recovery time  $t_{rr}=0.15\mu\text{s}$  max (B, C, E, G).  
 $t_{rr}=0.3\mu\text{s}$  max (J, L, N, R).
- Peak reverse voltage:  $V_{RM}=100$  to  $1500\text{V}$
- Average rectified current  $I_O=1.0\text{A}$

**Package Dimensions**

unit:mm

1175

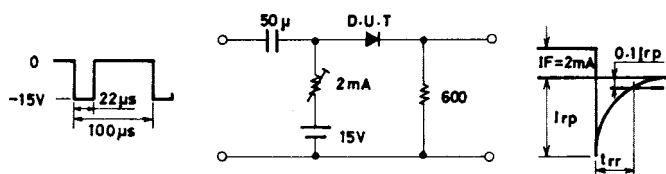
**Specifications****Absolute Maximum Ratings at  $T_a = 25^\circ\text{C}$** 

Parameter	Symbol	Conditions	DFH10TB	DFH10TC	DFH10TE	DFH10TG	Unit
Peak Reverse Voltage	$V_{RM}$		100	200	400	600	V
Average Rectified Current	$I_O$	$T_a=25^\circ\text{C}$	→	→	→	1.0	A
Surge Forward Current	$I_{FSM}$	50Hz sine wave, 1 cycle	→	→	→	60	A
Junction Temperature	$T_j$		→	→	→	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$		→	→	→	-40 to +150	$^\circ\text{C}$

Parameter	Symbol	Conditions	DFH10TJ	DFH10TL	DFH10TN	DFH10TR	Unit
Peak Reverse Voltage	$V_{RM}$		800	1000	1200	1500	V
Average Rectified Current	$I_O$	$T_a=25^\circ\text{C}$	→	→	→	1.0	A
Surge Forward Current	$I_{FSM}$	50Hz sine wave, 1 cycle	→	→	→	40	A
Junction Temperature	$T_j$		→	→	→	125	$^\circ\text{C}$
Storage Temperature	$T_{stg}$		→	→	→	-40 to +150	$^\circ\text{C}$

**Electrical Characteristics at  $T_a = 25^\circ\text{C}$** 

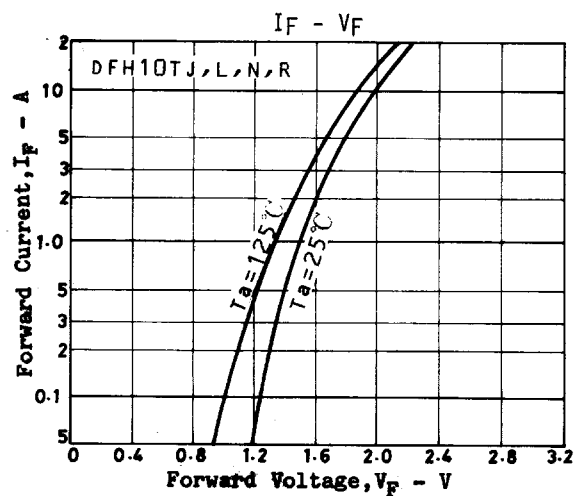
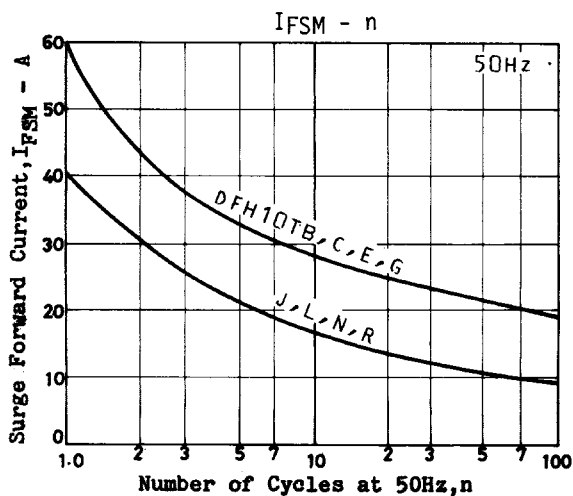
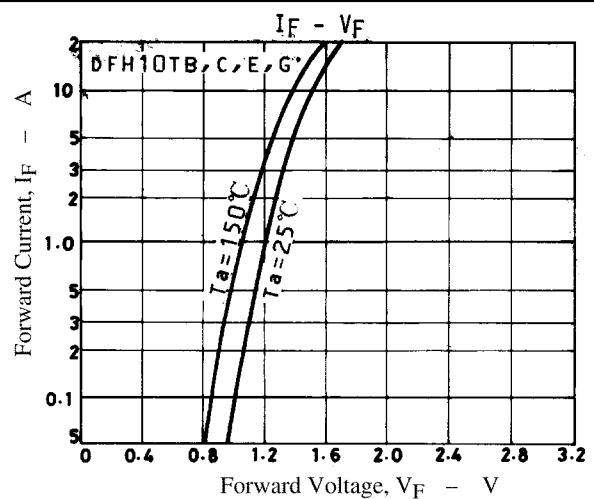
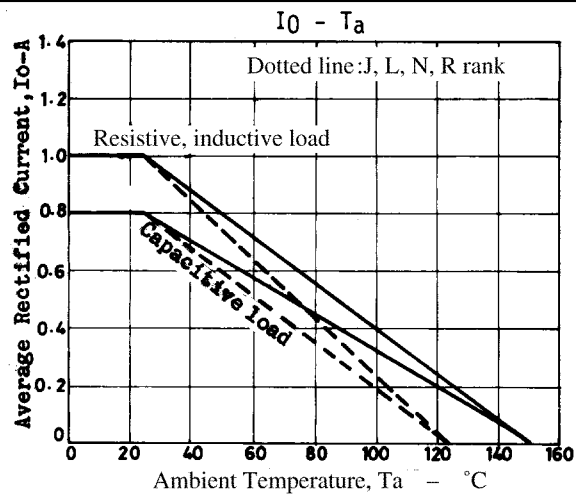
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Forward Voltage	$V_F$	$I_F=1.0\text{A}$ (B, C, E, G)			1.2	V
		$I_F=1.0\text{A}$ (J, L, N, R)			1.5	V
Reverse Current	$I_R$	$V_R$ : At each $V_{RM}$			10	$\mu\text{A}$
Reverse Recovery Time	$t_{rr}$	$I_F=2\text{mA}$ , $V_R=15\text{V}$ (B, C, E, G)			0.15	$\mu\text{s}$
		$I_F=2\text{mA}$ , $V_R=15\text{V}$ (J, L, N, R)			0.3	$\mu\text{s}$

**Reverse Recovery Time Test Circuit**Unit (resistance: $\Omega$ , capacitance:F)

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## DFH10T



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